



Vishay Siliconix

300 MHz, 2.5 Ω , Dual SPDT Analog Switches

DESCRIPTION

The DG3516, DG3517 are dual SPDT analog switches which operate from 1.8 V to 5.5 V single rail power supply. They are design for audio, video, and USB switching applications.

The devices have 2.5 Ω on-resistance and 300 MHz 3dB bandwidth. 0.2 Ω on-resistance matching and 1 Ω flatness make the device high linearity. The devices are 1.6 V logic compatible within the full operation voltage range.

These switches are built on a sub-micron high density process that brings low power consumption and low voltage performance.

The switches are packaged in MICRO FOOT chip scale package of 4 mm x 3 mm bump array.

As a committed partner to the community and environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switch products manufactured with tin/silver/copper (SnAgCu) device termination, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- 1.8 V to 5.5 V operation
- 2.5 Ω at 2.7 V R_{ON}
- 300 MHz 3 dB bandwidth
- ESD method 3015.7 > 2 kV
- Latch-up current 200 mA (JESD 78)
- 1.6 V logic compatible
- Compliant to RoHS Directive 2002/95/EC

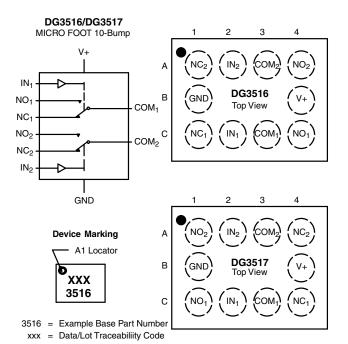
BENEFITS

- Space Saving MICRO FOOT[®] Package
- High Linearity
- Low Power Consumption
- · High Bandwidth
- Full Rail Signal Swing Range

APPLICATIONS

- Cellular Phones
- MP3
 - Media Players
 - Modems
 - Hard Drives
 - PCMCIA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp. Range	Package	Part Number				
- 40 °C to 85 °C	MICRO FOOT: 10 Bump (4 x 3, 0.5 mm Pitch, 238 μm Bump Height)	DG3516DB-T5-E1 DG3517DB-T5-E1				



COMPLIANT HALOGEN

Document Number: 73404 S11-1185-Rev. D, 13-Jun-11 www.vishay.com

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Reference V+ to GND	- 0.3 to + 6	N/				
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	V			
Continuous Current (NO, NC, COM)	± 100	mA				
Peak Current (Pulsed at 1 ms, 10 % du	ty cycle)	± 200	ma			
Storage Temperature	(D Suffix)	- 65 to 150	- °C			
Package Solder Reflow Conditions ^b	IR/Convection	250				
ESD per Method 3015.7		> 2	kV			
Power Dissipation (Packages) ^c	MICRO FOOT: 10 Bump (4 mm x 3 mm) ^d	457	mW			

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020B).

c. All bumps welded or soldered to PC board.

d. Derate 5.7 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+	= 3 V)								
		Test Conditions Otherwise Unless Specified			- 40	Limits - 40 °C to 85 °C			
Parameter	Symbol	V+ = 2.7 V to 3.6 V	$V_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^{e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit	
Analog Switch									
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}			Full	0		V+	v	
On-Resistance ^d	R _{ON}		V _{COM} = 1.5 V	Room Full		2.5	3.5 3.8		
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 2.7 V I _{NO} , I _{NC} = 10 mA	V+ = 2.7 V I _{NO} , I _{NC} = 10 mA	V _{COM} = 1, 1.5, 2 V	Room		0.52	1	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		V _{COM} = 1.5 V	Room			0.25		
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}		= 3.3 V,	Room Full	- 2 - 20		2 20	nA	
Switch On Leakage Suitchit	I _{COM(off)}	$V_{\rm NO}, V_{\rm NC} = 0.3 {\rm V/3}$	3 V, V _{COM} = 3 V/0.3 V	Room Full	- 2 - 20		2 20		
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 0.3 V/3 V		Room Full	- 2 - 20		2 20		
Digital Control									
Input High Voltage ^d	V _{INH}			Full	1.4			v	
Input Low Voltage	V _{INL}			Full			0.5] `	
Input Capacitance	C _{in}			Full		5		pF	
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V _{IN} = 0) V or V+	Full	1		1	μΑ	

www.vishay.com 2 Document Number: 73404 S11-1185-Rev. D, 13-Jun-11



DG3516, DG3517

Vishay Siliconix

SPECIFICATIONS (V+ = 3 V)								
		Test Conditions Otherwise Unless Specified			- 40	Limits °C to 85	5 °C	
Parameter	Symbol	V+ = 2.7 V to 3.6 V, V	′ _{IN} = 0.5 V or 1.4 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Dynamic Characteristics		•						
Turn-On Time	t _{ON}			Room Full		21	51 52	
Turn-Off Time	t _{OFF}		V+ = 2.7 V, V _{NO} or V _{NC} = 1.5 V R _L = 300 Ω, C _L = 35 pF			15	45 46	ns
Break-Before-Make Time	t _d			Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} =$	2 V, R_{GEN} = 0 Ω	Room		1		рС
Off-Isolation ^d	OIRR		f = 1 MHz	Room		- 74		
Off-Isolation-	UINN	$R_{L} = 50 \Omega, C_{L} = 5 pF$	f = 10 MHz	Room		- 54		dB
Crosstalk ^d	X _{TALK}		f = 1 MHz	Room		- 76		UD.
CIOSSIAIK	AIALK		f = 10 MHz	Room		- 56		
N _O , N _C Off Capacitance ^d	C _{NO(off)}			Room		12		
N _O , N _C OII Capacitance	C _{NC(off)}	$V_{\rm ext} = 0 \text{ or } V_{\rm e}$	f _ 1 M⊔z	Room		12		~ [
	C _{NO(on)}	– V _{IN} = 0 or V+, f = 1 MHz		Room		40		pF
Channel-On Capacitance ^d	C _{NC(on)}			Room		40		
Power Supply		•		•				•
Power Supply Current	l+	V _{IN} = 0 \	/ or V+	Room Full			1 1	μA

DG3516, DG3517

Vishay Siliconix



	= 5 V)	Test ConditionsOtherwise Unless SpecifiedV+ = 4.2 V to 5.5 V, V _{IN} = 0.8 V or 2 V ^e			Limits - 40 °C to 85 °C			
Parameter	Symbol			Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Uni
Analog Switch	-						1	
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}			Full	0		V+	v
On-Resistance ^d	R _{ON}		V _{COM} = 3.5 V	Room Full		2.2	2.9 3.1	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 4.2 V I _{NO} , I _{NC} = 10 mA	V _{COM} = 1, 2, 3.5 V	Room		0.53	1	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		V _{COM} = 3.5 V	Room			0.25	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}		= 5.5 V,	Room Full	- 2 - 20		2 20	
	I _{COM(off)}	V _{NO} , V _{NC} = 1 V/4.5	5 V, V _{COM} = 4.5 V/1 V	Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V _{NO} , V _N	_{IC} = V _{COM} = 1 V/4.5 V	Room Full	- 2 - 20		2 20	
Digital Control				_				
Input High Voltage ^d	V _{INH}			Full	2			v
Input Low Voltage	V _{INL}			Full			0.8	
Input Capacitance	C _{in}			Full		5		pF
Input Current	I _{INL} or I _{INH}	V _{IN} =	0 or V+	Full	1		1	μA
Dynamic Characteristics		•				•		
Turn-On Time	t _{ON}	$V_{+} - 42 V_{-} V_{+}$	_{NO} or V _{NC} = 3 V	Room Full		15	45 46	
Turn-Off Time	t _{OFF}		$P_{\rm L} = 35 \rm pF$	Room Full		12	42 43	ns
Break-Before-Make Time	t _d			Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN}$	= 2 V, R_{GEN} = 0 Ω	Room		1		pQ
Off-Isolation ^d	OIRR		f = 1 MHz	Room		- 74		
On-Isolation	Onn	$R_1 = 50 \Omega, C_1 = 5 pF$	f = 10 MHz	Room		- 54		dE
Crosstalk ^d	_		f = 1 MHz	Room		- 78		
			f = 10 MHz	Room		- 56		
N _O , N _C Off Capacitance ^d	C _{NO(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		12		-
	C _{NC(off)}			Room		12		pF
Channel-On Capacitance ^d	C _{NO(on)}			Room		40		-
	C _{NC(on)}			Room		40		
Power Supply				Room			4	
Power Supply Current	l+	$V_{IN} = 0$	$V_{IN} = 0 V \text{ or } V +$				1	μ/

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

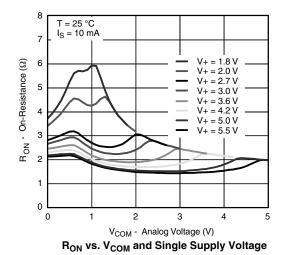
f. Guaranteed by 5 V testing, not production tested.

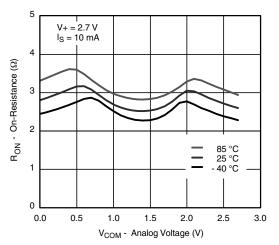
www.vishay.com 4 Document Number: 73404 S11-1185-Rev. D, 13-Jun-11



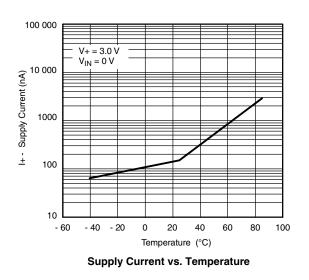
DG3516, DG3517 Vishay Siliconix

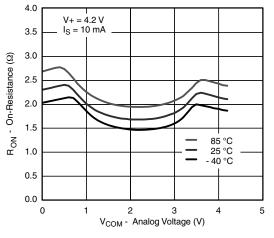
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



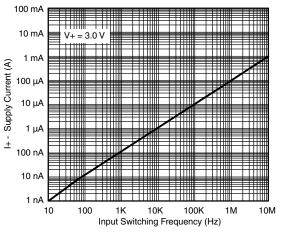


R_{ON} vs. Analog Voltage and Temperature





R_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Input Switching Frequency

Document Number: 73404 S11-1185-Rev. D, 13-Jun-11

www.vishay.com

5



2.4

XTALK

V+ = 3.0 V

 $R_L = 50 \Omega$

100M

V+ = 5.0 V

4

3

1G

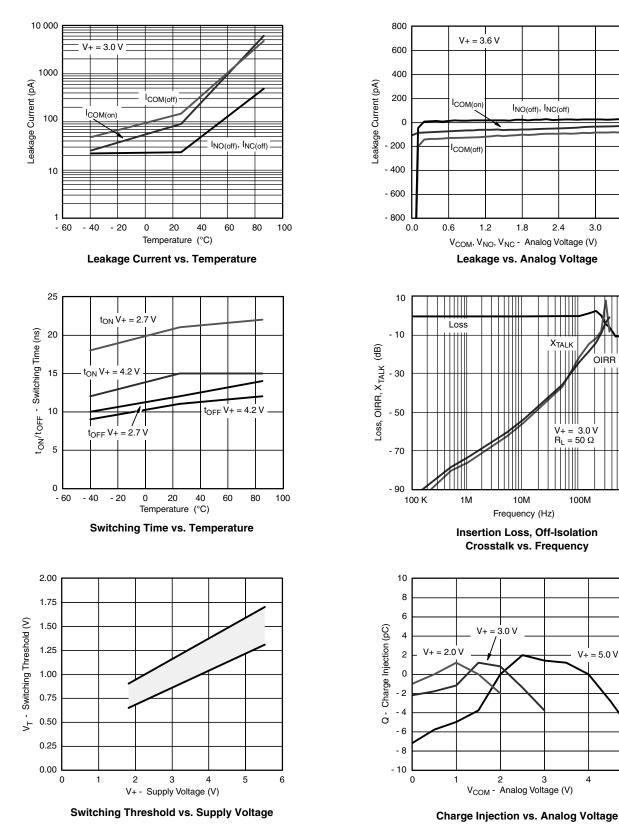
3.0

OIRR

3.6

Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





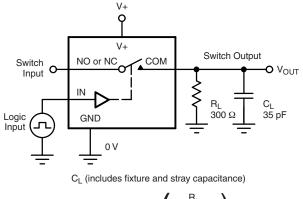
Document Number: 73404 S11-1185-Rev. D, 13-Jun-11

5

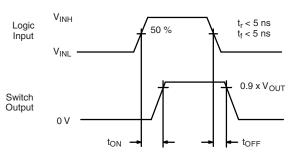


DG3516, DG3517 Vishay Siliconix

TEST CIRCUITS

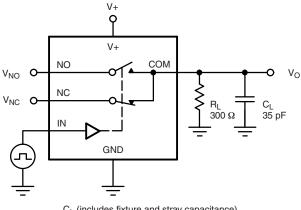


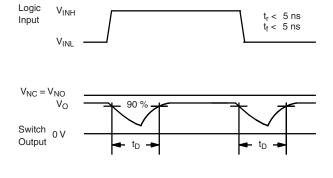




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

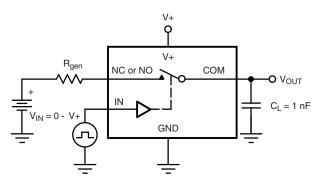


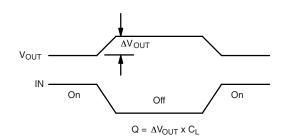




 $\ensuremath{\mathsf{C}}_L$ (includes fixture and stray capacitance)







IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

www.vishay.com

7

DG3516, DG3517

Vishay Siliconix

VISHAY,

TEST CIRCUITS

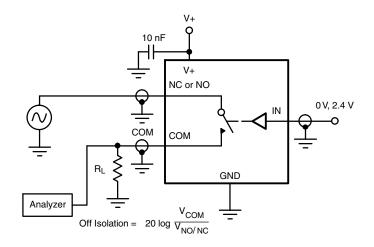


Figure 4. Off-Isolation

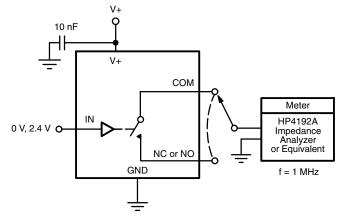


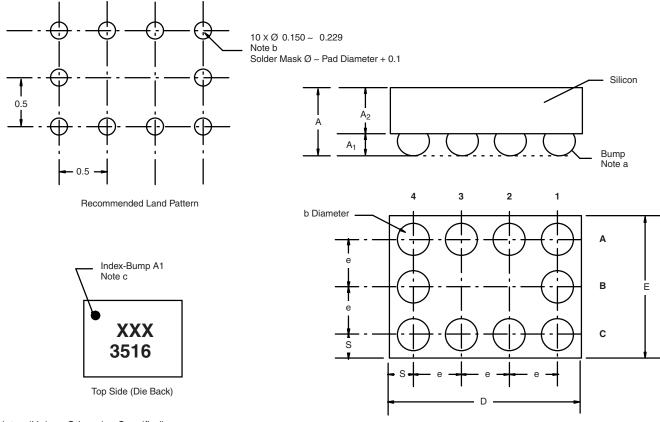
Figure 5. Channel Off/On Capacitance

www.vishay.com 8 Document Number: 73404 S11-1185-Rev. D, 13-Jun-11



PACKAGE OUTLINE

MICRO FOOT: 10 BUMP (4 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

a. Bump is Lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

Dim.	Millin	neters ^a	Inches		
	Min.	Max.	Min.	Max.	
Α	0.688	0.753	0.0271	0.0296	
A ₁	0.218	0.258	0.0086	0.0102	
A ₂	0.470	0.495	0.0185	0.0195	
b	0.306	0.346	0.0120	0.0136	
D	1.980	2.020	0.0780	0.0795	
E	1.480	1.520	0.0583	0.0598	
е	0.5 I	0.5 BASIC		BASIC	
S	0.230	0.270	0.0091	0.0106	

Notes:

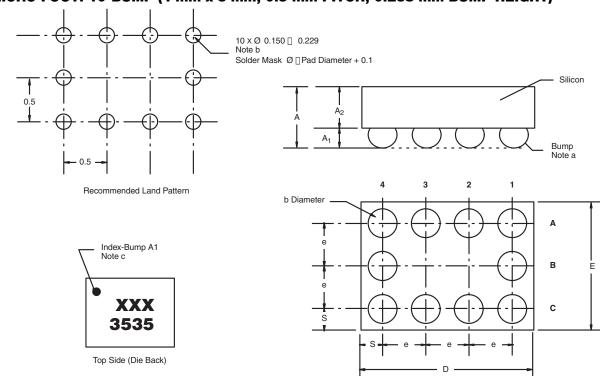
a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73404.

Document Number: 73404	
S11-1185-Rev. D, 13-Jun-11	

Vishay Siliconix





MICRO FOOT: 10-BUMP (4 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)

Notes

(unless otherwise specified)

a. Bump is lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

DIM.	MILLIM	ETERS ^a	INC	HES
Divi.	MIN.	MAX.	MIN.	MAX.
A	0.688	0.753	0.0271	0.0296
A ₁	0.218	0.258	0.0086	0.0102
A ₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.980	2.020	0.0780	0.0795
E	1.480	1.520	0.0583	0.0598
e	0.5 E	0.5 BASIC		BASIC
S	0.230	0.270	0.0091	0.0106

Note

a. Use millimeters as the primary measurement.

ECN: S11-1065-Rev. A, 13-Jun-11 DWG: 6001

www.vishay.com 1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.